

# **Complementary Power Transistors**

# **DPAK for Surface Mount Applications**

# MJD44H11 (NPN), MJD45H11 (PNP)

Designed for general purpose power and switching such as output or driver stages in applications such as switching regulators, converters, and power amplifiers.

#### **Features**

- Lead Formed for Surface Mount Application in Plastic Sleeves (No Suffix)
- Straight Lead Version in Plastic Sleeves ("-1" Suffix)
- Electrically Similar to Popular D44H/D45H Series
- Low Collector Emitter Saturation Voltage
- Fast Switching Speeds
- Complementary Pairs Simplifies Designs
- Epoxy Meets UL 94 V-0 @ 0.125 in
- NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

# **MAXIMUM RATINGS** (T<sub>A</sub> = 25°C, common for NPN and PNP, minus sign, "–", for PNP omitted, unless otherwise noted)

Rating	Symbol	Max	Unit
Collector-Emitter Voltage	$V_{CEO}$	80	Vdc
Emitter-Base Voltage	$V_{EB}$	5	Vdc
Collector Current - Continuous	Ic	8	Adc
Collector Current - Peak	I <sub>CM</sub>	16	Adc
Total Power Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	P <sub>D</sub>	20 0.16	W W/°C
Total Power Dissipation (Note 1) @ T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	1.75 0.014	W W/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
ESD – Human Body Model	HBM	3B	V
ESD - Machine Model	MM	С	V

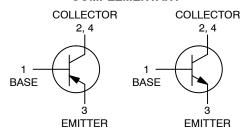
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

 These ratings are applicable when surface mounted on the minimum pad sizes recommended.

1

# SILICON POWER TRANSISTORS 8 AMPERES 80 VOLTS, 20 WATTS

#### **COMPLEMENTARY**









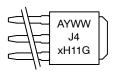
DPAK CASE 369C STYLE 1

DPAK CASE 369G STYLE 1

IPAK CASE 369D STYLE 1

#### **MARKING DIAGRAMS**





DPAK IPAK
A = Assembly Location

Y = Year WW = Work Week J4xH11 = Device Code x = 4 or 5

## **ORDERING INFORMATION**

Pb-Free Package

See detailed ordering and shipping information in the package dimensions section on page 7 of this data sheet.

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{ heta JC}$	6.25	°C/W
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	71.4	°C/W
Lead Temperature for Soldering	TL	260	°C

<sup>2.</sup> These ratings are applicable when surface mounted on the minimum pad sizes recommended.

### **ELECTRICAL CHARACTERISTICS**

 $(T_A = 25^{\circ}C, common for NPN and PNP, minus sign, "-", for PNP omitted, unless otherwise noted)$ 

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS	-		•	•	•
Collector–Emitter Sustaining Voltage (I <sub>C</sub> = 30 mA, I <sub>B</sub> = 0)	V <sub>CEO(sus)</sub>	80	-	-	Vdc
Collector Cutoff Current (V <sub>CE</sub> = Rated V <sub>CEO</sub> , V <sub>BE</sub> = 0)	I <sub>CES</sub>	-	-	1.0	μΑ
Emitter Cutoff Current (V <sub>EB</sub> = 5 Vdc)	I <sub>EBO</sub>	-	-	1.0	μА
ON CHARACTERISTICS					
Collector–Emitter Saturation Voltage (I <sub>C</sub> = 8 Adc, I <sub>B</sub> = 0.4 Adc)	V <sub>CE(sat)</sub>	_	-	1	Vdc
Base-Emitter Saturation Voltage (I <sub>C</sub> = 8 Adc, I <sub>B</sub> = 0.8 Adc)	V <sub>BE(sat)</sub>	_	-	1.5	Vdc
DC Current Gain ( $V_{CE} = 1 \text{ Vdc}, I_{C} = 2 \text{ Adc}$ ) ( $V_{CE} = 1 \text{ Vdc}, I_{C} = 4 \text{ Adc}$ )	h <sub>FE</sub>	60 40	- -	- -	-
DYNAMIC CHARACTERISTICS					
Collector Capacitance (V <sub>CB</sub> = 10 Vdc, f <sub>test</sub> = 1 Mhz) MJD44H11 MJD45H11	C <sub>cb</sub>	- -	45 130	- -	pF
Gain Bandwidth Product ( $I_C$ = 0.5 Adc, $V_{CE}$ = 10 Vdc, f = 20 Mhz) MJD44H11 MJD45H11	f <sub>T</sub>	- -	85 90	- -	MHz
SWITCHING TIMES				-	
Delay and Rise Times (I <sub>C</sub> = 5 Adc, I <sub>B1</sub> = 0.5 Adc) MJD44H11 MJD45H11	t <sub>d</sub> + t <sub>r</sub>	- -	300 135	- -	ns
Storage Time ( $I_C$ = 5 Adc, $I_{B1}$ = $I_{B2}$ = 0.5 Adc) MJD44H11 MJD45H11	t <sub>s</sub>	- -	500 500	- -	ns
Fall Time (I <sub>C</sub> = 5 Adc, I <sub>B1</sub> = I <sub>B2</sub> = 0.5 Adc) MJD44H11 MJD45H11	t <sub>f</sub>	<u>-</u> -	140 100	- -	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

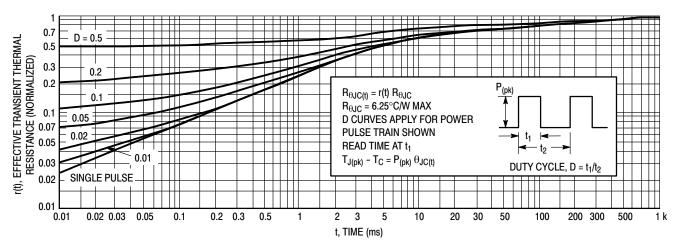


Figure 1. Thermal Response

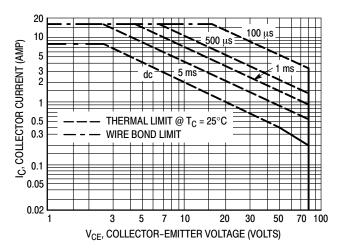


Figure 2. Maximum Forward Bias Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate  $I_C$  –  $V_{CE}$  limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 2 is based on  $T_{J(pk)} = 150^{\circ} C$ ;  $T_{C}$  is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided  $T_{J(pk)} \le 150^{\circ} C$ .  $T_{J(pk)}$  may be calculated from the data in Figure 1. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

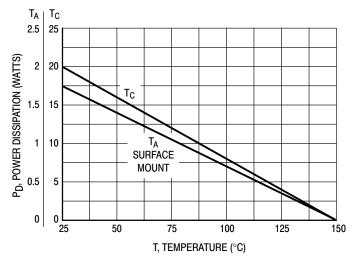


Figure 3. Power Derating

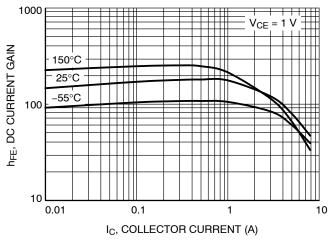


Figure 4. MJD44H11 DC Current Gain

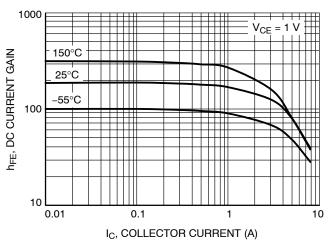


Figure 5. MJD45H11 DC Current Gain

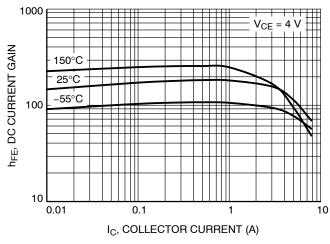


Figure 6. MJD44H11 DC Current Gain

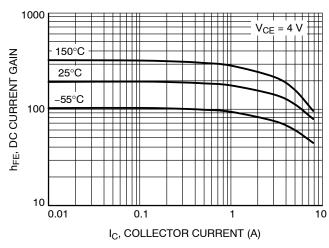


Figure 7. MJD45H11 DC Current Gain

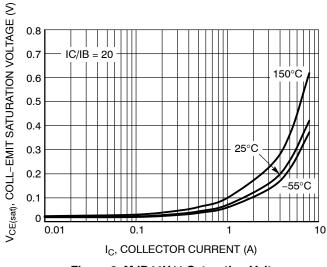


Figure 8. MJD44H11 Saturation Voltage  $V_{CE(sat)}$ 

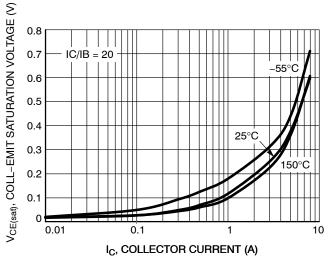


Figure 9. MJD45H11 Saturation Voltage  $V_{CE(sat)}$ 

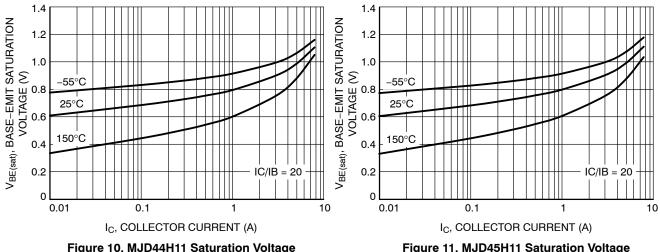


Figure 10. MJD44H11 Saturation Voltage  $V_{BE(sat)}$ 

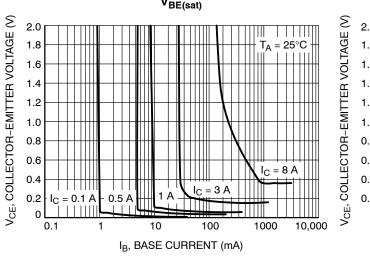


Figure 12. MJD44H11 Collector Saturation Region

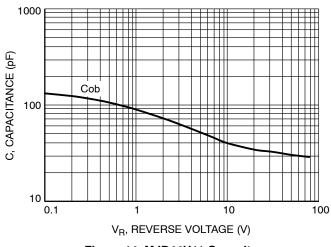


Figure 14. MJD44H11 Capacitance



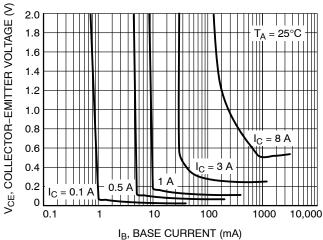


Figure 13. MJD45H11 Collector Saturation Region

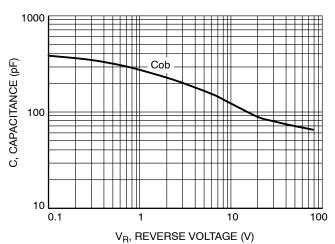


Figure 15. MJD45H11 Capacitance

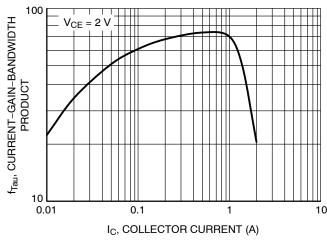


Figure 16. MJD44H11 Current-Gain-Bandwidth Product

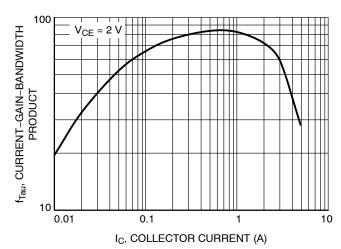


Figure 17. MJD45H11 Current-Gain-Bandwidth Product

### **ORDERING INFORMATION**

Device	Package Type	Package	Shipping <sup>†</sup>
MJD44H11G	DPAK (Pb-Free)	369C	75 Units / Rail
NJVMJD44H11G	DPAK (Pb-Free)	369C	75 Units / Rail
MJD44H11-1G	DPAK-3 (Pb-Free)	369D	75 Units / Rail
MJD44H11RLG	DPAK (Pb-Free)	369C	1,800 / Tape & Reel
NJVMJD44H11RLG*	DPAK (Pb-Free)	369C	1,800 / Tape & Reel
MJD44H11T4G	DPAK (Pb-Free)	369C	2,500 / Tape & Reel
NJVMJD44H11T4G*	DPAK (Pb-Free)	369C	2,500 / Tape & Reel
MJD44H11T5G	DPAK (Pb-Free)	369C	2,500 / Tape & Reel
MJD45H11G	DPAK (Pb-Free)	369C	75 Units / Rail
NJVMJD45H11G*	DPAK (Pb-Free)	369C	75 Units / Rail
MJD45H11-1G	DPAK-3 (Pb-Free)	369D	75 Units / Rail
MJD45H11RLG	DPAK (Pb-Free)	369C	1,800 / Tape & Reel
NJVMJD45H11RLG*	DPAK (Pb-Free)	369C	1,800 / Tape & Reel
MJD45H11T4G	DPAK (Pb-Free)	369C	2,500 / Tape & Reel
NJVMJD45H11T4G*	DPAK (Pb-Free)	369C	2,500 / Tape & Reel
NJVMJD44H11D3T4G*	DPAK (Pb-Free)	369G	2,500 / Tape & Reel
NJVMJD45H11D3T4G*	DPAK (Pb-Free)	369G	2,500 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
\*NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP

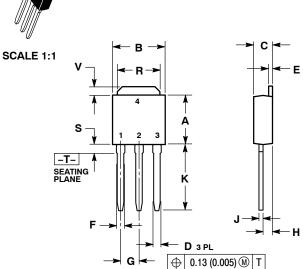
Capable

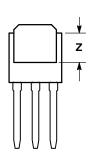
# **MECHANICAL CASE OUTLINE**





**DATE 15 DEC 2010** 





#### NOTES:

- DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.235	0.245	5.97	6.35
В	0.250	0.265	6.35	6.73
С	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.018	0.023	0.46	0.58
F	0.037	0.045	0.94	1.14
G	0.090	BSC	2.29	BSC
Н	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.350	0.380	8.89	9.65
R	0.180	0.215	4.45	5.45
S	0.025	0.040	0.63	1.01
٧	0.035	0.050	0.89	1.27
Z	0.155		3.93	

#### **MARKING DIAGRAMS**

STYLE 1: PIN 1. BASE 2. COLLECTOR **EMITTER** 3 COLLECTOR STYLE 6: PIN 1. MT1 2. MT2 3. GATE STYLE 5: PIN 1. GATE

2. ANODE 3. CATHODE

ANODE

STYLE 2: PIN 1. GATE 2. DRAIN SOURCE 3 4. DRAIN

MT2

4. CATHODE STYLE 7: PIN 1. GATE 2. COLLECTOR

STYLE 3: PIN 1. ANODE

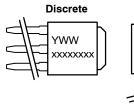
3. EMITTER COLLECTOR

2. CATHODE

3 ANODE

STYLE 4: PIN 1. CATHODE

 ANODE
 GATE 4. ANODE



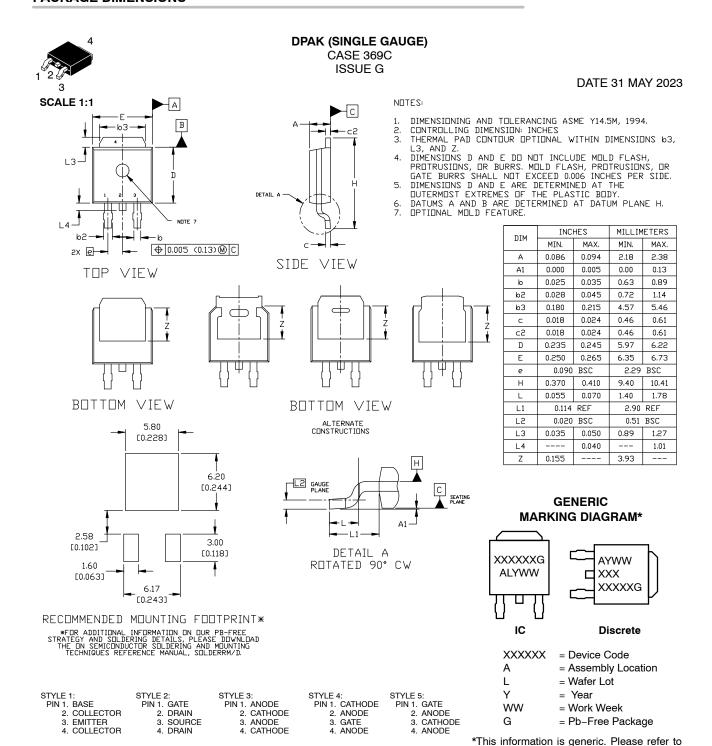


xxxxxxxxx = Device Code Α = Assembly Location IL = Wafer Lot Υ = Year WW = Work Week

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DESCRIPTION:	DPAK (SINGLE GAUGE)		PAGE 1 OF 1

STYLE 10:

PIN 1. CATHODE 2. ANODE

3 CATHODE

4. ANODE

STYLE 9:

PIN 1. ANODE 2. CATHODE

3 RESISTOR ADJUST

CATHODE

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STYLE 7: PIN 1. GATE 2. COLLECTOR

3 FMITTER

4. COLLECTOR

STYLE 8:

PIN 1. N/C 2. CATHODE

3 ANODE

CATHODE

STYLE 6:

PIN 1. MT1 2. MT2

3 GATE

device data sheet for actual part marking.

Pb-Free indicator, "G" or microdot "■", may

or may not be present. Some products may

not follow the Generic Marking.

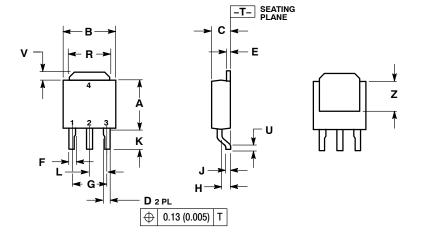




#### **DPAK-3, SURFACE MOUNT** CASE 369G-01 ISSUE O

**DATE 23 DEC 2003** 

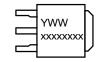
# SCALE 1:1



- NOTES:
  1. DIMENSIONING AND TOLERANCING
- PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIM	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.235	0.245	5.97	6.22
В	0.250	0.265	6.35	6.73
С	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.018	0.023	0.46	0.58
F	0.037	0.045	0.94	1.14
G	0.180	BSC	4.58 BSC	
Н	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.102	0.114	2.60	2.89
L	0.090 BSC		2.29	BSC
R	0.180	0.215	4.57	5.45
U	0.020		0.51	
V	0.035	0.050	0.89	1.27
Z	0.155		3.93	

### **GENERIC MARKING DIAGRAM\***



xxxxxxxxx = Device Code Υ = Year ww = Work Week

STYLE 1:	STYLE 2:	STYLE 3:	STYLE 4:
PIN 1. BASE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
2. COLLECTOR	2. DRAIN	2. CATHODE	2. ANODE
3. EMITTER	3. SOURCE	3. ANODE	3. GATE
4. COLLECTOR	4. DRAIN	4. CATHODE	4. ANODE
STYLE 5:	STYLE 6:	STYLE 7:	
PIN 1. GATE	PIN 1. MT1	PIN 1. GATE	
2. ANODE	2. MT2	2. COLLECTOR	
3. CATHODE	3. GATE	3. EMITTER	
4. ANODE	4. MT2	4. COLLECTOR	

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DESCRIPTION:	DPAK-3, SURFACE MOUN	IT	PAGE 1 OF 1

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<sup>\*</sup>This information is generic. Please refer to device data sheet for actual part marking.

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